AMENDMENTS TO THE CLAIMS

(Currently amended) A resist composition comprising a resin component (A) that
undergoes a change in alkali solubility in the presence of acid, and an acid generator component
 (B) that generates acid on exposure, wherein

said resin component (A) has a weight average molecular weight of no more than 8,000 and comprises structural units (a) derived from a (meth)acrylate ester; and

said component (B) comprises at-least-one a sulfonium compound represented by a general formula (b-1) or a general formula (b-2) shown below:

[Formula 1]

$$R^{2}$$
 S^{+} N SO_{2} X ... (b-1)

$$R^1$$
 O_2S-Y
 R^2-S^+ N $(b-2)$
 R^3 O_2S-Z

[wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represent, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; R^1 to R^3 each represent, independently, an aryl group or an alkyl group, and at least one of R^1 to R^3 represents an aryl group].

 (Previously presented) A resist composition according to claim 1, wherein said component (B) further comprises an onium salt-based acid generator comprising a straight-chain fluorinated alkylsulfonate anion of 1 to 7 carbon atoms.

- 3. (Previously presented) A resist composition according to claim 1, wherein said structural units (a) comprise structural units (a1) derived from a (meth)acrylate ester comprising an acid dissociable, dissolution inhibiting group.
- 4. (Previously presented) A resist composition according to claim 3, wherein said structural units (a) further comprise structural units (a2) derived from a (meth)acrylate ester comprising a lactone-containing monocyclic or polycyclic group.
- (Previously presented) A resist composition according to claim 3, wherein said structural units (a) further comprise structural units (a3) derived from a (meth)acrylate ester comprising a polar group-containing aliphatic hydrocarbon group.
- (Original) A resist composition according to claim 1, further comprising a nitrogencontaining organic compound.
- 7. (Previously presented) A method for forming a resist pattern, comprising the steps of forming a resist film on a substrate using a resist composition according to claim 1; conducting selective exposure treatment of said resist film; and alkali developing said resist film to form said resist pattern.

8. (Canceled)

9. (New) A resist composition comprising a resin component (A) that undergoes a change in alkali solubility in the presence of acid, and an acid generator component (B) that generates acid on exposure, wherein:

said resin component (A) has a weight average molecular weight of no more than 7,500 and comprises structural units (a) derived from a (meth)acrylate ester,

wherein said structural units (a) comprise structural units (a1) derived from a (meth)acrylate ester containing an acid dissociable, dissolution inhibiting group,

structural units (a2) derived from a (meth)acrylate ester comprising a lactone-containing monocyclic or polycyclic group, and

> structural units (a3) derived from a (meth)acrylate ester comprising a hydroxyl groupcontaining aliphatic hydrocarbon group; and wherein

said component (B) comprises at least one sulfonium compound represented by a general formula (b-1) or a general formula (b-2) shown below:

[Formula 1]

$$R^{2}$$
 R^{3} R^{3}

$$R^1$$
 O_2S-Y R^2-S^+ N ... $(b-2)$ R^3 O_2S-Z

[wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represents, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; R^1 to R^3 each represents, independently, an aryl group or an alkyl group, and at least one of R^1 to R^3 represents an aryl group].

- 10. (New) A resist composition according to claim 9, wherein said component (B) further comprises an onium salt-based acid generator comprising a straight-chain fluorinated alkylsulfonate anion of 1 to 7 carbon atoms.
- (New) A resist composition according to claim 9, further comprising a nitrogencontaining organic compound.
- 12. (New) A method for forming a resist pattern, comprising the steps of forming a resist film on a substrate using a resist composition according to claim 9; conducting selective exposure treatment of said resist film; and alkali developing said resist film to form said resist pattern.

13. (New) A resist composition, comprising a resin component (A) that undergoes a change in alkali solubility in the presence of acid, and an acid generator component (B) that generates acid on exposure, wherein

said resin component (A) has a weight average molecular weight of no more than 8,000 and comprises structural units (a) derived from a (meth)acrylate ester;

said component (B) comprises at least one sulfonium compound represented by a general formula (b-1) or a general formula (b-2) shown below:

[Formula 1]

$$R^{2}$$
 S^{+} S^{0} S^{0} S^{0} S^{0} S^{0} S^{0}

$$R^1$$
 O_2S-Y R^2-S^+ N ... $(b-2)$ R^3 O_2S-Z

[wherein, X represents an alkylene group of 2 to 6 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; Y and Z each represents, independently, an alkyl group of 1 to 10 carbon atoms in which at least one hydrogen atom has been substituted with a fluorine atom; \mathbb{R}^1 to \mathbb{R}^3 each represents, independently, an aryl group or an alkyl group, and at least one of \mathbb{R}^1 to \mathbb{R}^3 represents an aryl group]; and

an onium salt-based acid generator comprising a straight-chain fluorinated alkylsulfonate anion of 1 to 7 carbon atoms, wherein the blend ratio (weight ratio) between the onium salt-based acid generator and the one or more compounds selected from the sulfonium compounds is within a range from 1:9 to 9:1.

14. (New) A resist composition according to claim 13, wherein said structural units (a) comprise structural units (a1) derived from a (meth)acrylate ester comprising an acid dissociable, dissolution inhibiting group.

- 15. (New) A resist composition according to claim 14, wherein said structural units (a) further comprise structural units (a2) derived from a (meth)acrylate ester comprising a lactone-containing monocyclic or polycyclic group.
- 16. (New) A resist composition according to claim 14, wherein said structural units (a) further comprise structural units (a3) derived from a (meth)acrylate ester comprising a polar group-containing aliphatic hydrocarbon group.
- 17. (New) A resist composition according to claim 13, further comprising a nitrogencontaining organic compound.
- 18. (New) A method for forming a resist pattern, comprising the steps of forming a resist film on a substrate using a resist composition according to claim 13; conducting selective exposure treatment of said resist film; and alkali developing said resist film to form said resist pattern.